Highly-dense Mixed Grained Reconfigurable Architecture with Via-switch

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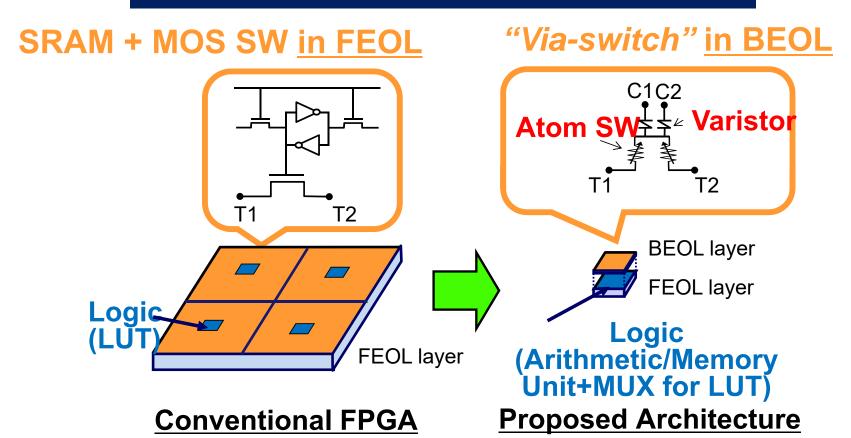
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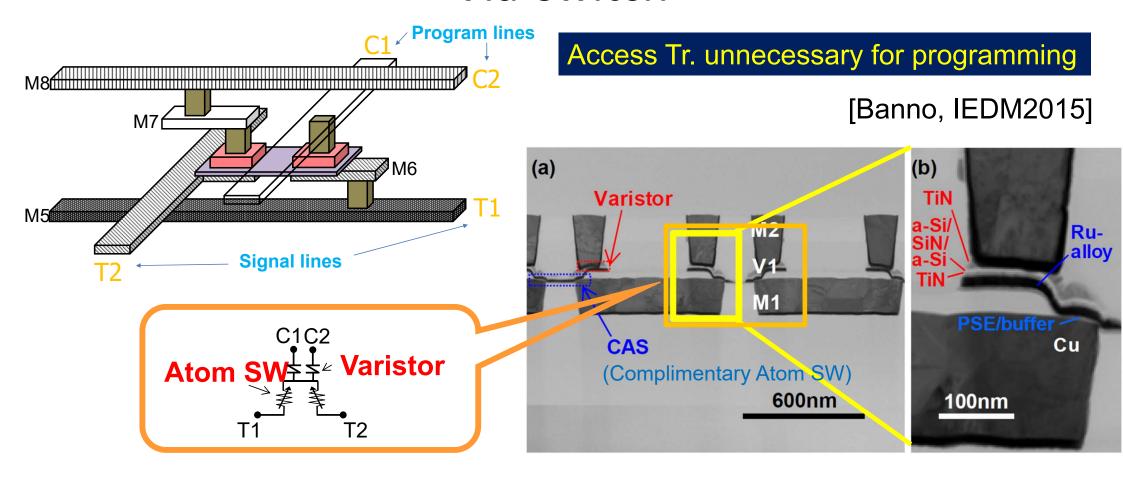
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Contribution

26X higher density 66% smaller interconnect delay at 0.5V



Via-switch



Atom SW: Electrochemical nonvolatile R-change device On-R can be reduced to 200Ω .

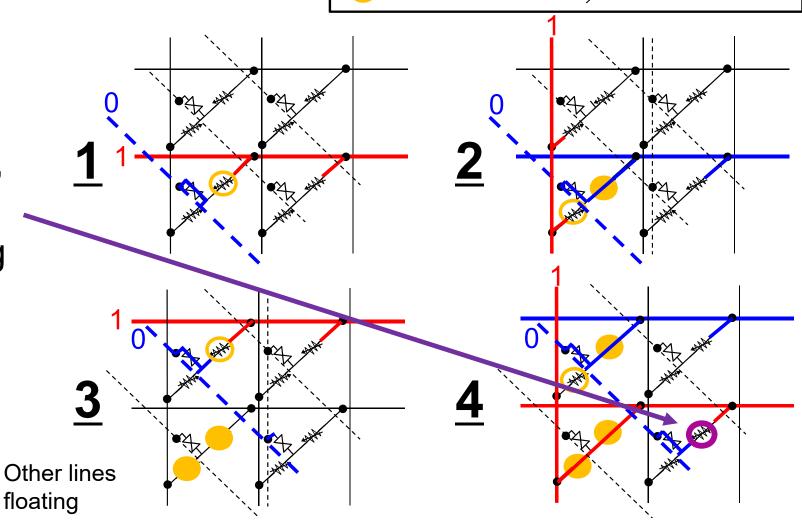
Why two program lines?

Atom SW under intentional programming

Atom SW under unintentional programming

On-state Atom SW 🦟 Off-state Atom SW

With a single program line, unintentional programming will happen.



Why two program lines?

Atom SW under programming

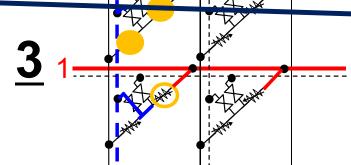
On-state atom SW

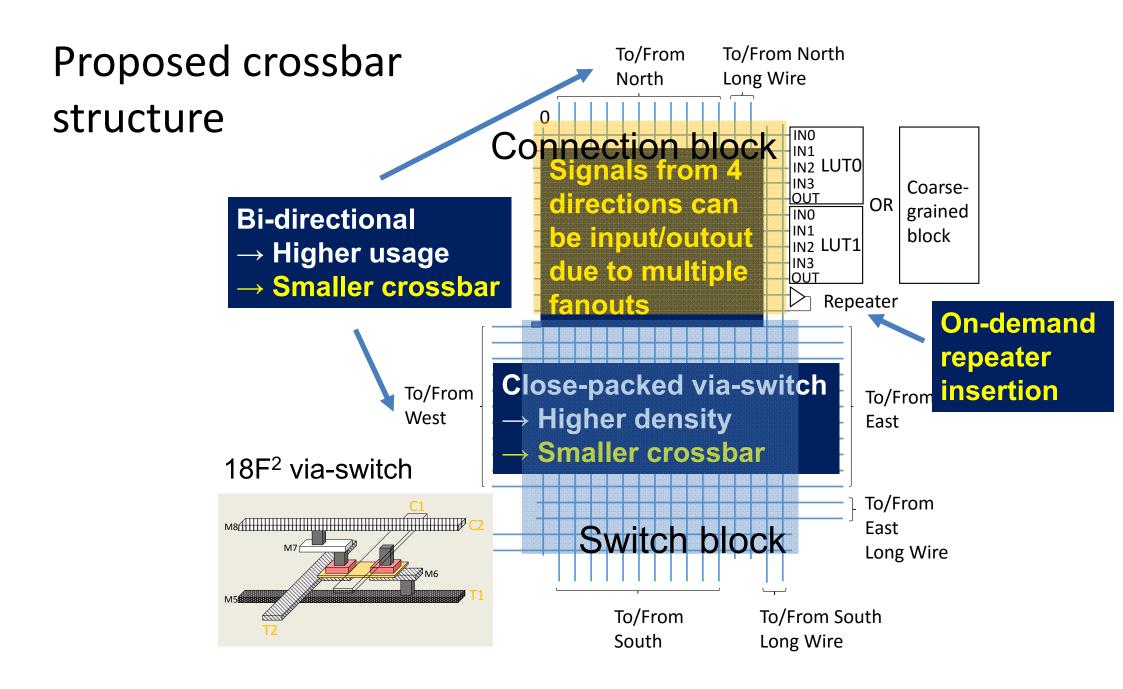
Off-state atom SW

With two program lines, unintentional programming will not happen.

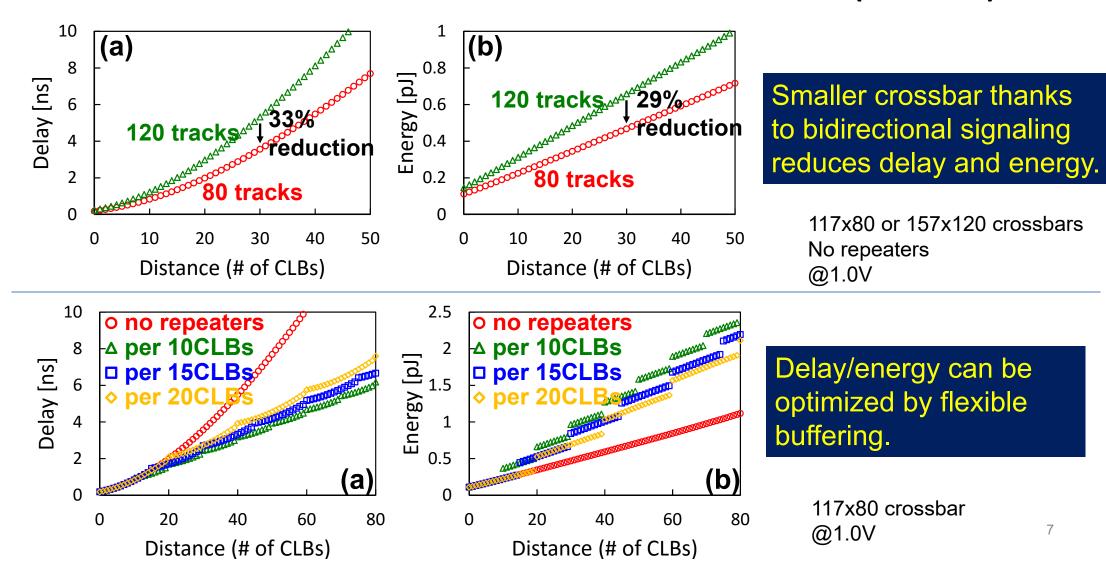
Multiple-ON in a column enables multiple fanouts.

> Other lines floating

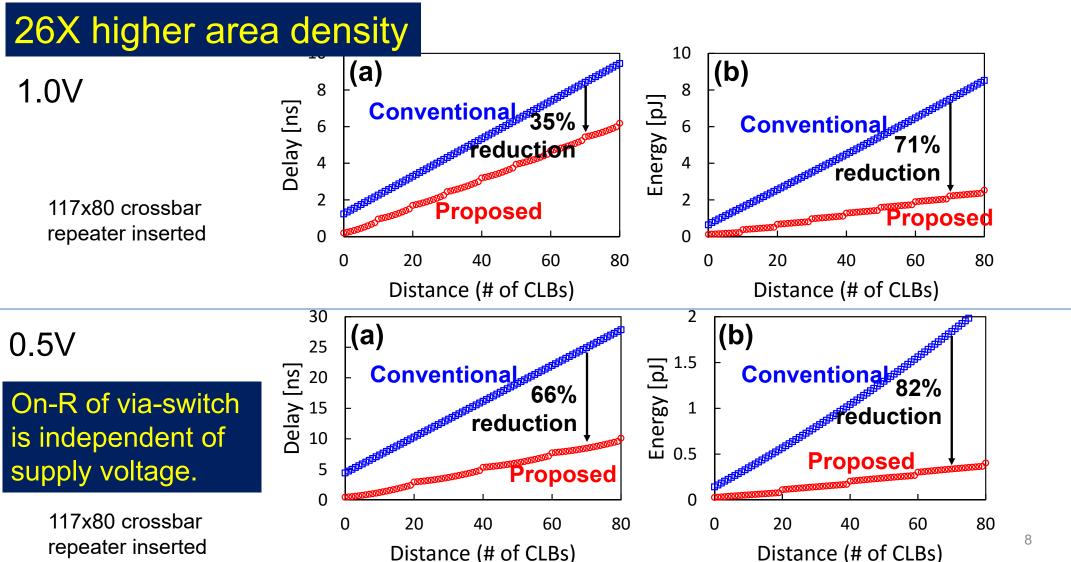




Interconnect Performance Evaluation (65nm)



Comparison w/ SRAM-based FPGA (TMG+SRAM crossbar)



Conclusion

- Proposed a highly-dense reconfigurable architecture that exploits via-switch.
 - 26X higher density
 - Interconnection delay is reduced by 35% (1.0V) and 66% (0.5V)
 - Interconnection energy is reduced by 71% (1.0V) and 82% (0.5V)
- Future works
 - Import long wire interconnection
 - Application mapping and performance evaluation